

## SN74LVC1G08-Q1 単一 2 入力の正論理 AND ゲート

### 1 特長

- 車載アプリケーション用にAEC-Q100認定済み:
  - デバイス温度グレード1:  $-40^{\circ}\text{C} \sim +125^{\circ}\text{C}$ 、 $T_A$
- 5V  $V_{CC}$  動作に対応
- 過電圧許容の入力により 5.5V までの電圧に対応
- $V_{CC}$  への降圧変換をサポート
- 低消費電力、最大  $I_{CC}$  10 $\mu\text{A}$
- 3.3V において  $\pm 24\text{mA}$  の出力駆動能力
- $I_{off}$  により活線挿抜、部分的パワーダウン・モード、バック・ドライブ保護をサポート
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能
- JESD 22を超えるESD保護
  - 2000V、人体モデル(A114-A)
  - 200V、マシン・モデル(A115-A)
  - 1000V、デバイス帯電モデル(C101)

### 2 アプリケーション

- 車載アプリケーション用に完全な認定済み
- 複数の電力レールのパワー・グッド信号を結合
- 条件が真になるまで信号の通過を抑止
- アクティブ LOW エラー信号の結合

### 3 概要

この単一 2 入力の正 AND ゲートは、1.65V~5.5V の  $V_{CC}$  で動作するよう設計されています。

SN74LVC1G08-Q1 デバイスは、ブール関数  $Y = A \cdot B$  or  $Y = \overline{A + B}$  を正論理で実行します。

このデバイスは、 $I_{off}$  を使用する部分的パワーダウン・アプリケーション用に完全に動作が規定されています。 $I_{off}$  回路が出力をディセーブルするため、電源オフ時にデバイスに電流が逆流して損傷を引き起こすことを防止できます。

CMOS デバイスは出力駆動能力が大きく、広い  $V_{CC}$  動作範囲にわたって、静止電力消費が低く保たれます。

SN74LVC1G08 は、本体サイズ 1.45mm  $\times$  1.00mm の小型 DRY パッケージなど、各種のパッケージで供給されます。

#### 製品情報<sup>(1)</sup>

型番	パッケージ	本体サイズ
SN74LVC1G08Q	SOT-23 (5)	2.90mm $\times$ 1.60mm
	SC70 (5)	2.00mm $\times$ 1.25mm
	SON (6) 事前情報	1.45mm $\times$ 1.00mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



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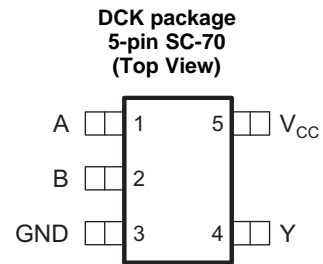
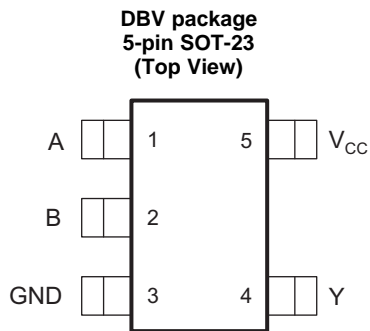
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## 4 改訂履歴

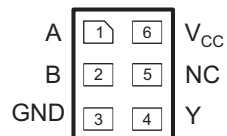
資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision F (April 2008) から Revision G に変更	Page
• データシートを新しい TI フォーマットに変更 .....	1
• 「製品情報」表に DRY パッケージを追加 .....	1
• Added <i>Thermal Information</i> table. ....	5
• Added <i>Typical Characteristics</i> . ....	7
• Added <i>Detailed Description</i> section. ....	10
• Added <i>Application and Implementation</i> section. ....	11
• Added <i>Power Supply Recommendations</i> section. ....	12
• Added <i>Layout</i> section. ....	12

## 5 Pin Configuration and Functions



**DRY package - Advance Information  
6-pin SON  
(Top View)**



NC – No internal connection

See mechanical drawings for dimensions.

### Pin Functions

NAME	PIN		I/O	DESCRIPTION
	NO. DBV, DCK	NO. DRY		
A	1	1	Input	Input A
B	2	2	Input	Input B
GND	3	3	—	Ground
Y	4	4	Output	Output Y
V <sub>CC</sub>	5	6	—	Positive Supply
NC		5	—	No internal connection

## 6 Specifications

### 6.1 Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range	–0.5	6.5	V
V <sub>I</sub>	Input voltage range <sup>(2)</sup>	–0.5	6.5	V
V <sub>O</sub>	Voltage range applied to any output in the high-impedance or power-off state <sup>(2)</sup>	–0.5	6.5	V
V <sub>O</sub>	Voltage range applied to any output in the high or low state <sup>(2)(3)</sup>	–0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0	–50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0	–50	mA
I <sub>O</sub>	Continuous output current		±50	mA
	Continuous current through V <sub>CC</sub> or GND		±100	mA
T <sub>J</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature	–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of V<sub>CC</sub> is provided in the *Recommended Operating Conditions* table.

### 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 <sup>(1)</sup> HBM ESD Classification Level	±2000	V
		Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

### 6.3 Recommended Operating Conditions<sup>(1)</sup>

		MIN	MAX	UNIT	
V <sub>CC</sub>	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		
		V <sub>CC</sub> = 3 V to 3.6 V	2		
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>		
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	
		V <sub>CC</sub> = 3 V to 3.6 V		0.8	
		V <sub>CC</sub> = 4.5 V to 5.5 V		0.3 × V <sub>CC</sub>	
V <sub>I</sub>	Input voltage	0	5.5	V	
V <sub>O</sub>	Output voltage	0	V <sub>CC</sub>	V	
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 1.65 V		–4	mA
		V <sub>CC</sub> = 2.3 V		–8	
		V <sub>CC</sub> = 3 V		–16	
		V <sub>CC</sub> = 4.5 V		–24	
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 1.65 V		4	mA
		V <sub>CC</sub> = 2.3 V		8	
		V <sub>CC</sub> = 3 V		16	
		V <sub>CC</sub> = 4.5 V		24	
Δt/Δv	Input transition rise or fall rate	V <sub>CC</sub> = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V <sub>CC</sub> = 3.3 V ± 0.3 V		10	
		V <sub>CC</sub> = 5 V ± 0.5 V		5	
T <sub>A</sub>	Operating free-air temperature	Q-suffix devices	–40	125	°C
		I-suffix devices	–40	85	°C

(1) All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>	SN74LVC1G08-Q1			UNIT	
	DBV	DCK	DRY - Advance Information		
	5 PINS	5 PINS	6 PINS		
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	209.4	244.2	264.4	°C/W
R <sub>θJctop</sub>	Junction-to-case (top) thermal resistance	132.5	156.1	166.6	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	118.1	130.8	142.2	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	48.8	47.2	26.1	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	117.4	130.0	141.6	°C/W
R <sub>θJcbot</sub>	Junction-to-case (bottom) thermal resistance	–	–	–	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics application report](#).

## 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	–40°C to 85°C			–40°C to 125°C RECOMMENDED			UNIT
			MIN	TYP <sup>(1)</sup>	MAX	MIN	TYP	MAX	
V <sub>OH</sub>	I <sub>OH</sub> = –100 μA	1.65 V to 5.5 V	V <sub>CC</sub> – 0.1			V <sub>CC</sub> – 0.15			V
	I <sub>OH</sub> = –4 mA	1.65 V	1.2			1.2			
	I <sub>OH</sub> = –8 mA	2.3 V	1.9			1.9			
	I <sub>OH</sub> = –16 mA	3 V	2.4			2.4			
	I <sub>OH</sub> = –24 mA		2.3			2.3			
	I <sub>OH</sub> = –32 mA	4.5 V	3.8			3.8			
V <sub>OL</sub>	I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V				0.1			V
	I <sub>OL</sub> = 4 mA	1.65 V				0.45			
	I <sub>OL</sub> = 8 mA	2.3 V				0.3			
	I <sub>OL</sub> = 16 mA	3 V				0.4			
	I <sub>OL</sub> = 24 mA					0.55			
	I <sub>OL</sub> = 32 mA	4.5 V				0.55			
I <sub>I</sub>	A or B inputs	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±5			μA
I <sub>off</sub>		V <sub>I</sub> or V <sub>O</sub> = 5.5 V	0			±10			μA
I <sub>CC</sub>		V <sub>I</sub> = 5.5 V or GND, I <sub>O</sub> = 0	1.65 V to 5.5 V			10			μA
ΔI <sub>CC</sub>		One input at V <sub>CC</sub> – 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 5.5 V			500			μA
C <sub>i</sub>		V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V			4			pF

 (1) All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.

## 6.6 Switching Characteristics, T<sub>A</sub> = –40°C to 125°C

 over recommended operating free-air temperature range (unless otherwise noted) (see [Figure 3](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 125°C								UNIT
			V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A or B	Y	1	10	1	7.5	1	6.5	1	6	ns

## 6.7 Switching Characteristics, T<sub>A</sub> = –40°C to 85°C

 over recommended operating free-air temperature range, (unless otherwise noted) (see [Figure 4](#))

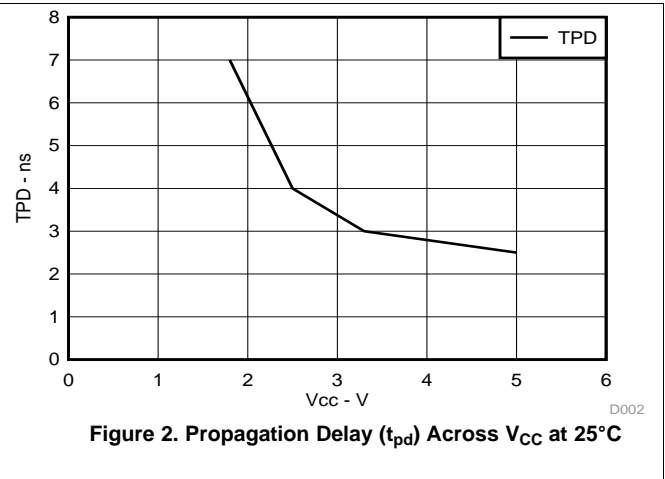
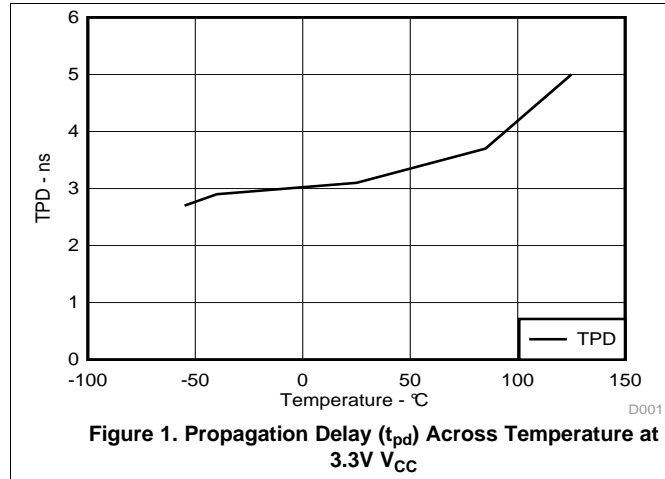
PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 85°C								UNIT
			V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A or B	Y	2.4	8	1.1	5.5	1	4.5	1	4	ns

## 6.8 Operating Characteristics

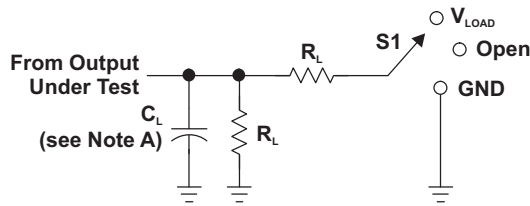
 T<sub>A</sub> = 25°C

PARAMETER	TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT	
		TYP	TYP	TYP	TYP		
C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz	21	24	26	31	pF

## 6.9 Typical Characteristics



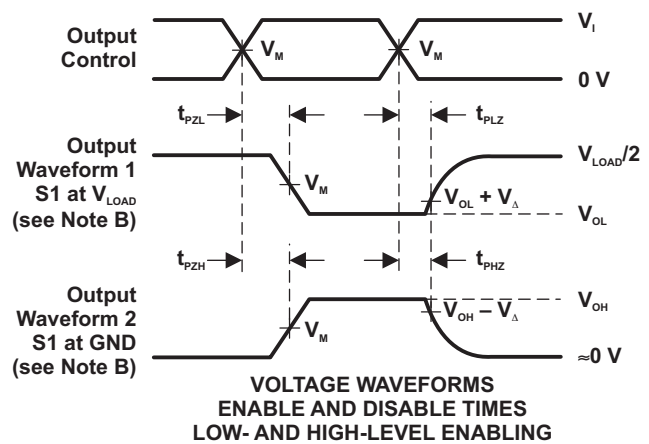
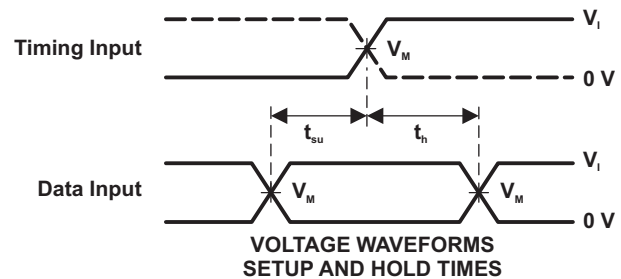
## 7 Parameter Measurement Information



LOAD CIRCUIT

TEST	S1
$t_{PLH}/t_{PHL}$	Open
$t_{PLZ}/t_{PZL}$	$V_{LOAD}$
$t_{PHZ}/t_{PZH}$	GND

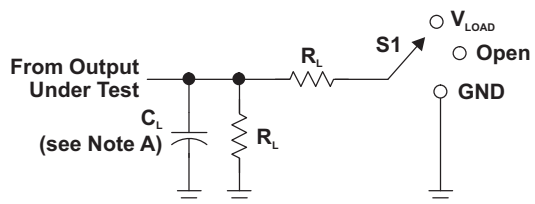
$V_{CC}$	INPUTS		$V_M$	$V_{LOAD}$	$C_L$	$R_L$	$V_{\Delta}$
	$V_i$	$t_r/t_f$					
$1.8\text{ V} \pm 0.15\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M $\Omega$	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M $\Omega$	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	15 pF	1 M $\Omega$	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	$V_{CC}$	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M $\Omega$	0.3 V



- NOTES: A.  $C_L$  includes probe and jig capacitance.  
 B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.  
 C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_o = 50\ \Omega$ .  
 D. The outputs are measured one at a time, with one transition per measurement.  
 E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .  
 F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .  
 G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .  
 H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

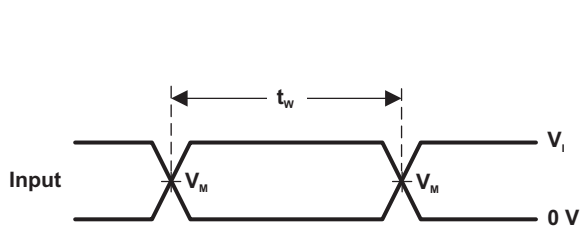
Parameter Measurement Information (continued)



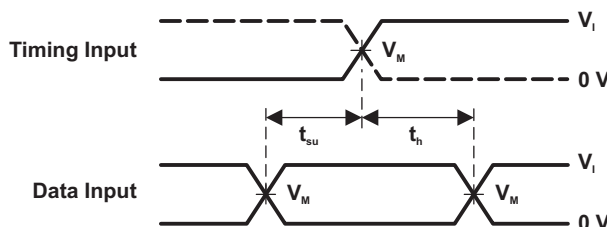
LOAD CIRCUIT

TEST	S1
$t_{PLH}/t_{PHL}$	Open
$t_{PLZ}/t_{PZL}$	$V_{LOAD}$
$t_{PHZ}/t_{PZH}$	GND

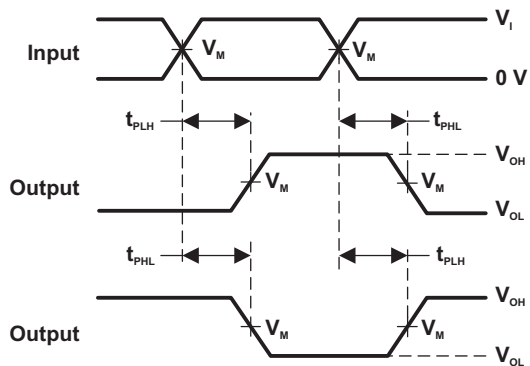
$V_{CC}$	INPUTS		$V_M$	$V_{LOAD}$	$C_L$	$R_L$	$V_{\Delta}$
	$V_I$	$t_r/t_f$					
$1.8\text{ V} \pm 0.15\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k $\Omega$	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 $\Omega$	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 $\Omega$	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	$V_{CC}$	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 $\Omega$	0.3 V



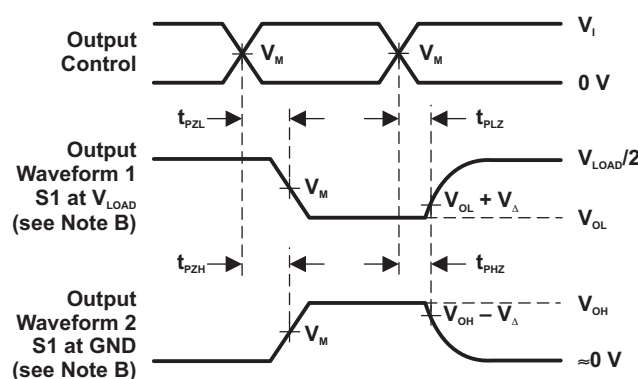
VOLTAGE WAVEFORMS PULSE DURATION



VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_o = 50\ \Omega$ .
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{on}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
  - H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

## 8 Detailed Description

### 8.1 Overview

The SN74LVC1G08Q device contains one 2-input positive AND gate device and performs the Boolean function  $Y = A \cdot B$  or  $Y = \overline{\overline{A} + \overline{B}}$ . This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

### 8.2 Functional Block Diagram

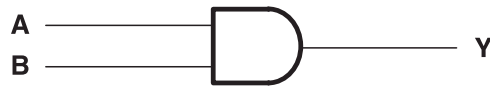


Figure 5. Positive Logic

### 8.3 Feature Description

- Wide operating voltage range.
  - Operates from 1.65 V to 5.5 V.
- Allows down voltage translation.
- Inputs accept voltages to 5.5 V.
- I<sub>off</sub> feature allows voltages on the inputs and outputs when V<sub>CC</sub> is 0 V.

### 8.4 Device Functional Modes

Table 1. Function Table

INPUTS		OUTPUT Y
A	B	
H	H	H
L	X	L
X	L	L

## 9 Application and Implementation

### 9.1 Application Information

The SN74LVC1G08Q is a high-drive CMOS device that can be used for implementing AND logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5 V tolerant allowing it to translate down to  $V_{CC}$ .

### 9.2 Typical Application

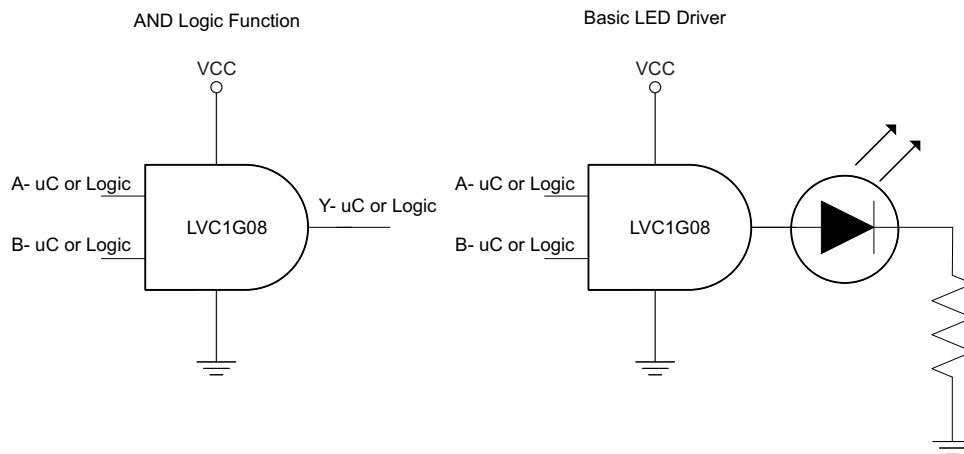


Figure 6. Typical Application Example

#### 9.2.1 Design Requirements

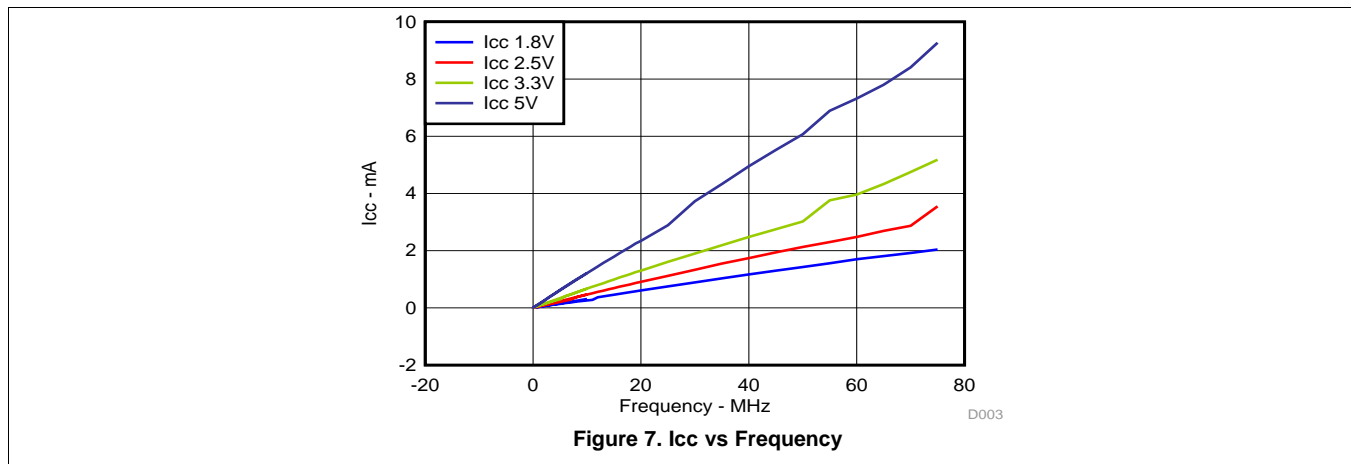
This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

#### 9.2.2 Detailed Design Procedure

1. Recommended Input Conditions
  - Rise time and fall time specs. See  $(\Delta t/\Delta V)$  in the [Recommended Operating Conditions](#) table.
  - Specified high and low levels. See  $(V_{IH}$  and  $V_{IL})$  in the [Recommended Operating Conditions](#) table.
  - Inputs are overvoltage tolerant allowing them to go as high as  $(V_I \text{ max})$  in the [Recommended Operating Conditions](#) table at any valid  $V_{CC}$ .
2. Recommend Output Conditions
  - Load currents should not exceed  $(I_O \text{ max})$  per output and should not exceed total current (continuous current through  $V_{CC}$  or GND) for the part. These limits are located in the [Absolute Maximum Ratings](#) table.
  - Outputs should not be pulled above  $V_{CC}$ .

## Typical Application (continued)

### 9.2.3 Application Curves



## 10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each V<sub>cc</sub> pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu$ F capacitor is recommended and if there are multiple V<sub>cc</sub> pins then 0.01- $\mu$ F or 0.022- $\mu$ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

## 11 Layout

### 11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to Gnd or V<sub>cc</sub> whichever make more sense or is more convenient.

### 11.2 Layout Example



Figure 8. Layout Example

## 12 デバイスおよびドキュメントのサポート

### 12.1 商標

All trademarks are the property of their respective owners.

### 12.2 静電気放電に関する注意事項



これらのデバイスは、限定的なESD(静電破壊)保護機能を内蔵しています。保存時または取り扱い時は、MOSゲートに対する静電破壊を防止するために、リード線同士をショートさせておくか、デバイスを導電フォームに入れる必要があります。

### 12.3 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

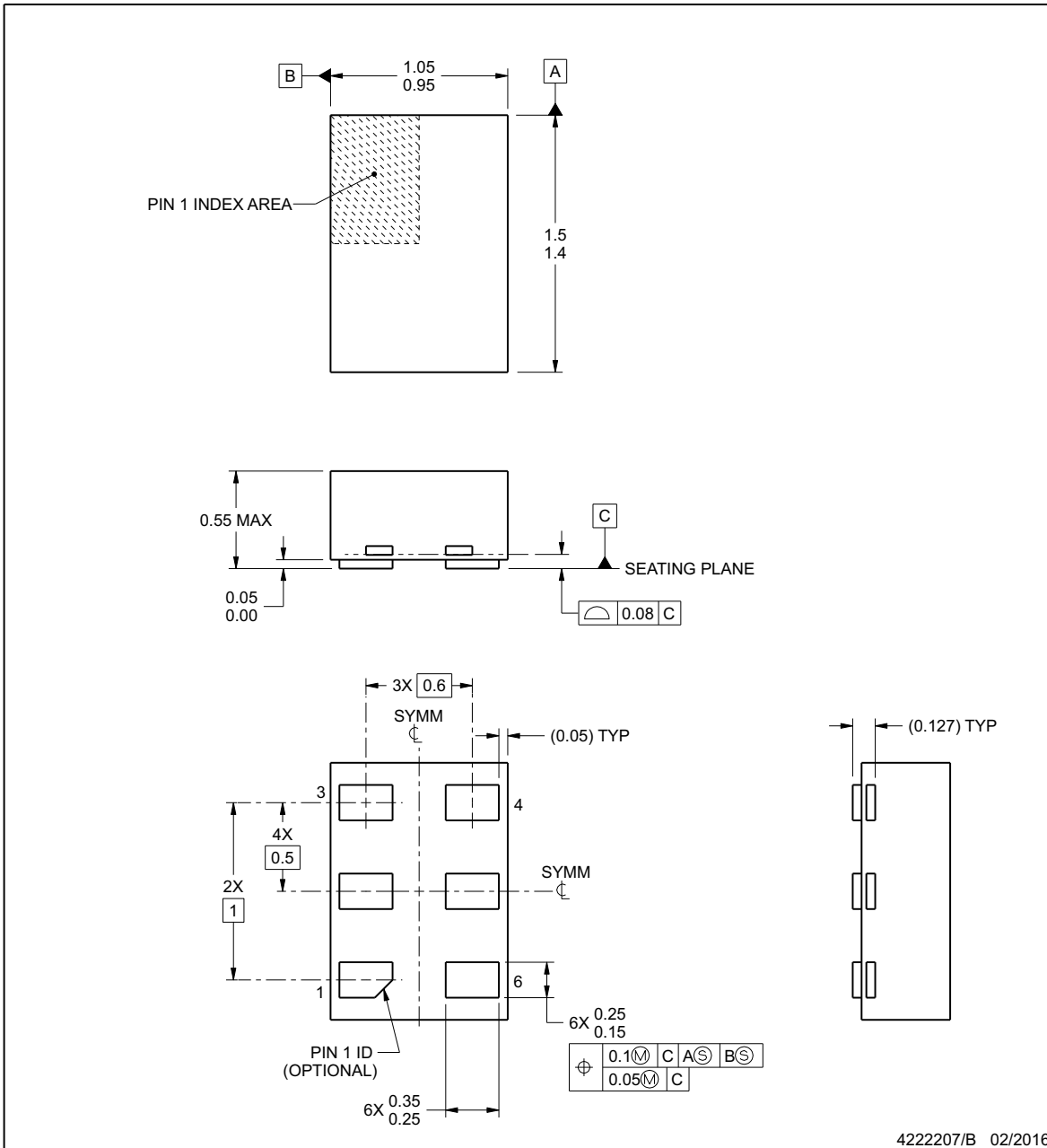


**PACKAGE OUTLINE**

**DRY0006B**

**USON - 0.55 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



**NOTES:**

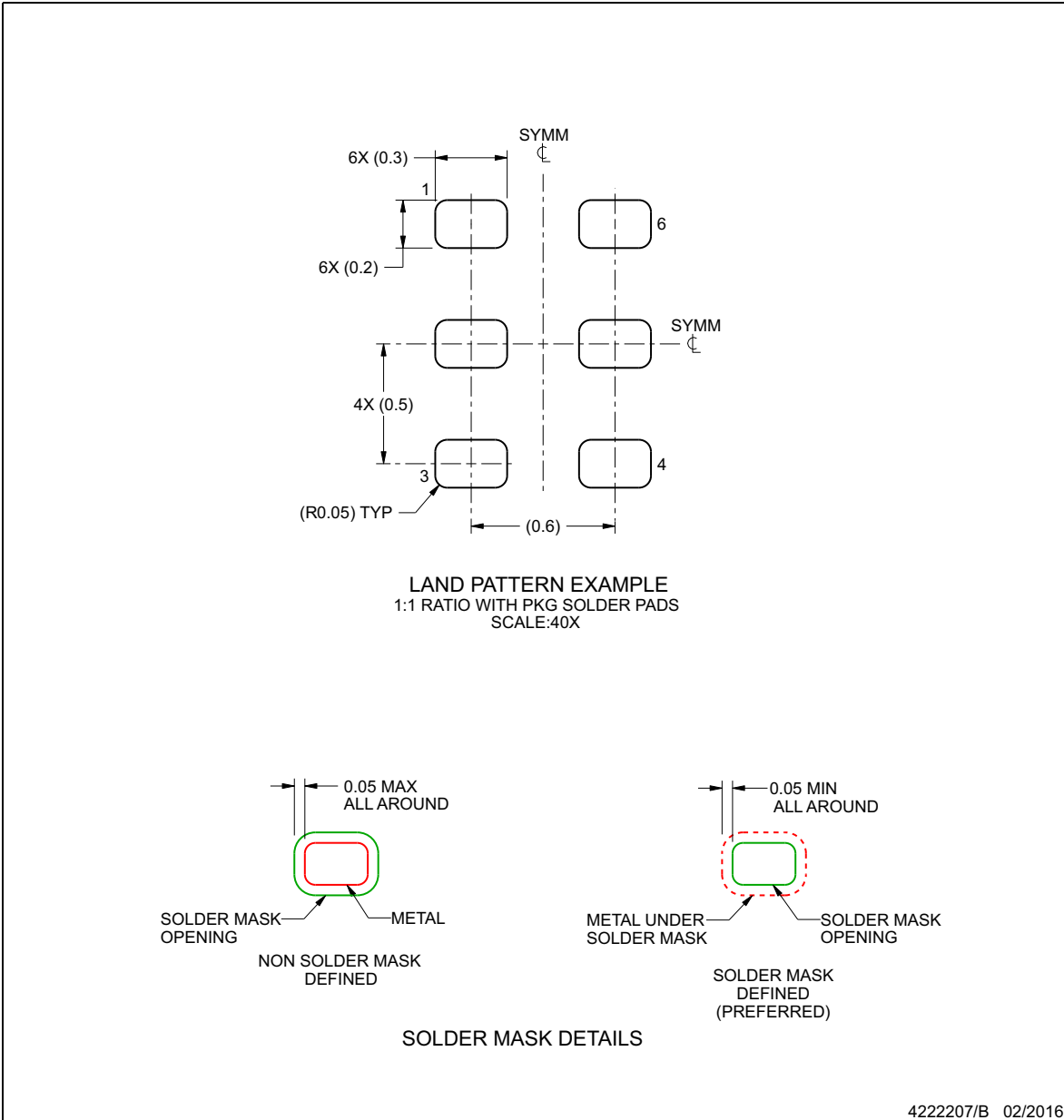
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

**EXAMPLE BOARD LAYOUT**

**DRY0006B**

**USON - 0.55 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

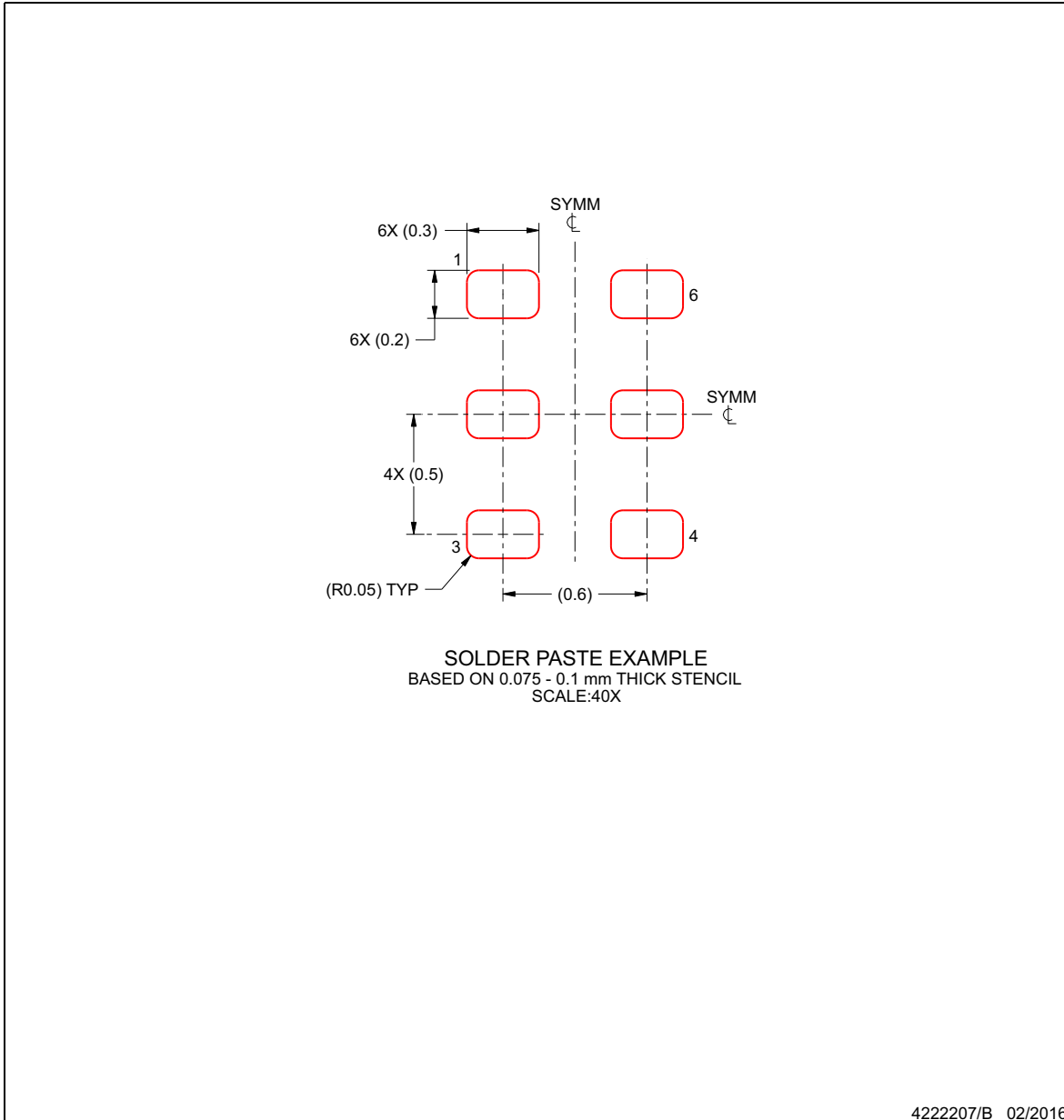
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).

**EXAMPLE STENCIL DESIGN**

**DRY0006B**

**USON - 0.55 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

- 4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
74LVC1G08QDBVRQ1G4	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
74LVC1G08QDBVRQ1G4.B	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
74LVC1G08QDCKRQ1G4	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CEO
74LVC1G08QDCKRQ1G4.B	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CEO
SN74LVC1G08IDCKRQ1	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	CEO
SN74LVC1G08IDCKRQ1.A	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	CEO
SN74LVC1G08IDCKRQ1.B	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	CEO
SN74LVC1G08QDBVRQ1	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
SN74LVC1G08QDBVRQ1.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
SN74LVC1G08QDBVRQ1.B	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
SN74LVC1G08QDCKRQ1	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(CEJ, CEO)
SN74LVC1G08QDCKRQ1.A	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(CEJ, CEO)
SN74LVC1G08QDCKRQ1.B	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(CEJ, CEO)
SN74LVC1G08QDRYRQ1	Active	Production	SON (DRY)   6	5000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	EM
SN74LVC1G08QDRYRQ1.B	Active	Production	SON (DRY)   6	5000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	EM

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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**OTHER QUALIFIED VERSIONS OF SN74LVC1G08-Q1 :**

- Catalog : [SN74LVC1G08](#)
- Enhanced Product : [SN74LVC1G08-EP](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC1G08QDBVRQ1G4	SOT-23	DBV	5	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
74LVC1G08QDBVRQ1G4	SOT-23	DBV	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
74LVC1G08QDCKRQ1G4	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08IDCKRQ1	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08IDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDRYRQ1	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC1G08QDBVRQ1G4	SOT-23	DBV	5	3000	200.0	183.0	25.0
74LVC1G08QDBVRQ1G4	SOT-23	DBV	5	3000	180.0	180.0	18.0
74LVC1G08QDCKRQ1G4	SC70	DCK	5	3000	200.0	183.0	25.0
SN74LVC1G08IDCKRQ1	SC70	DCK	5	3000	210.0	185.0	35.0
SN74LVC1G08IDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0
SN74LVC1G08QDBVRQ1	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	190.0	190.0	30.0
SN74LVC1G08QDRYRQ1	SON	DRY	6	5000	189.0	185.0	36.0

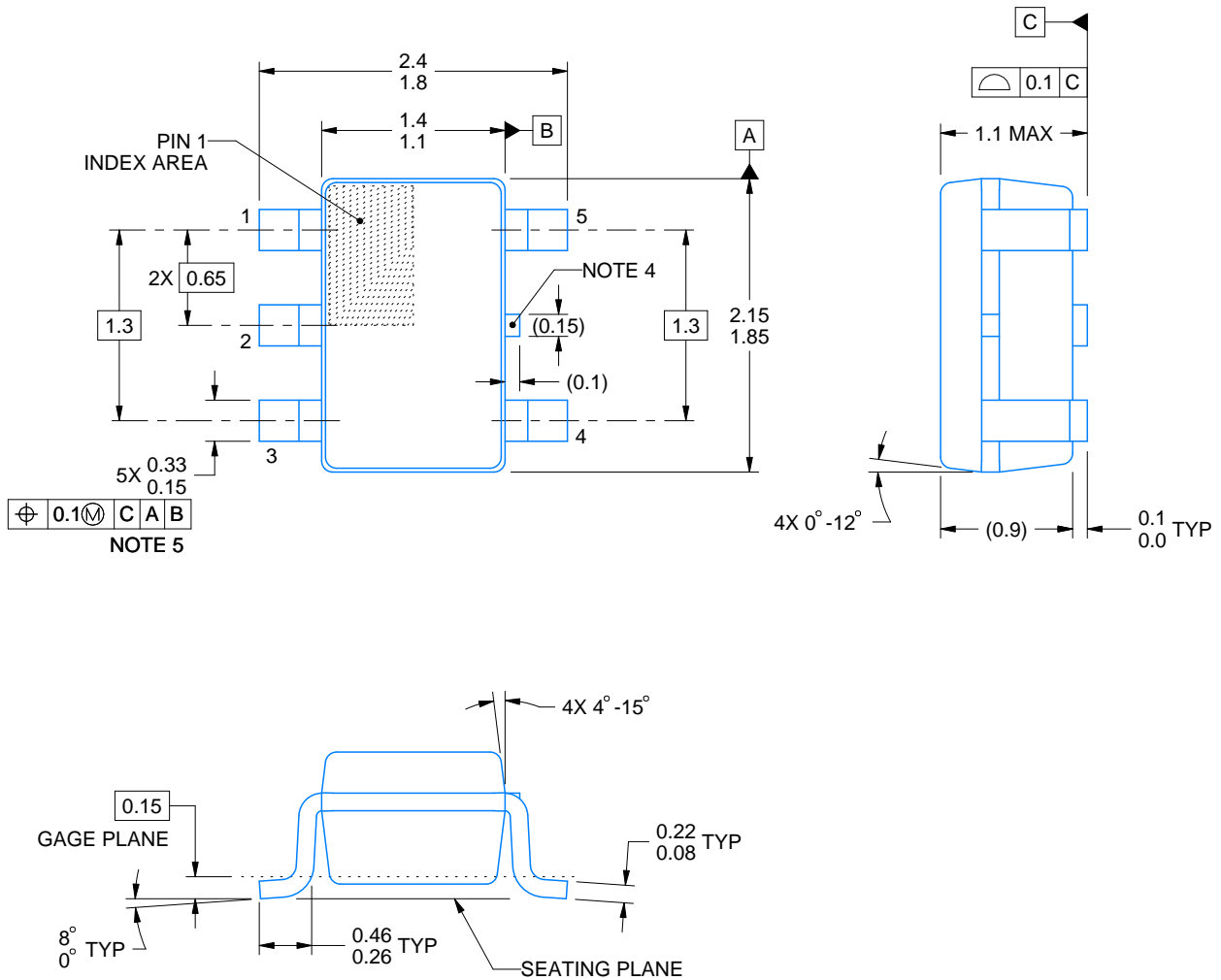
# DCK0005A



# PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/G 11/2024

## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

# EXAMPLE BOARD LAYOUT

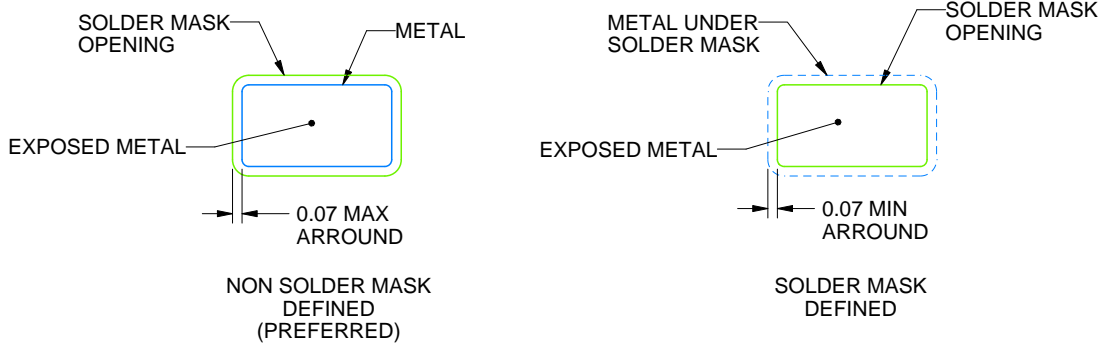
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:18X



SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

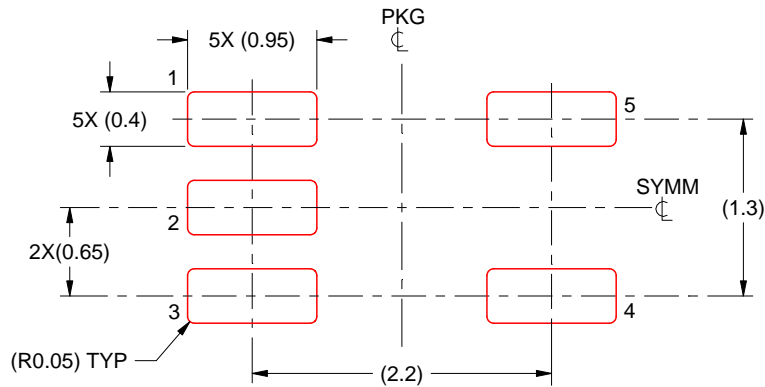
- 7. Publication IPC-7351 may have alternate designs.
- 8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 THICK STENCIL  
SCALE: 18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.



# EXAMPLE BOARD LAYOUT

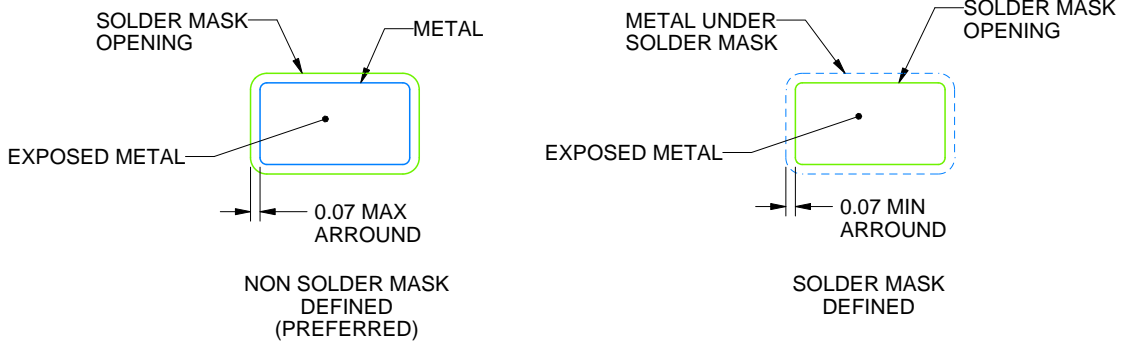
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## GENERIC PACKAGE VIEW

**DRY 6**

**USON - 0.6 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4207181/G

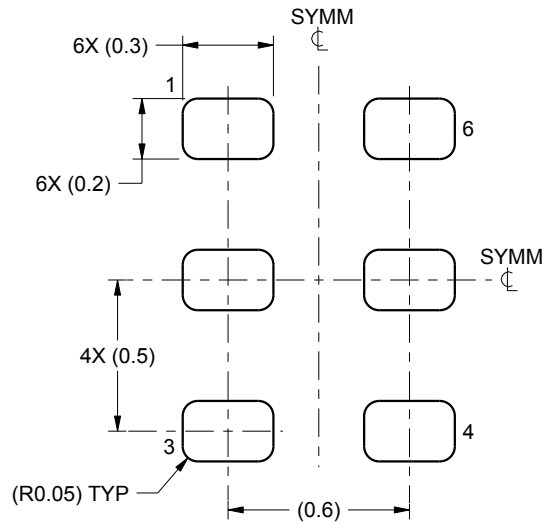


# EXAMPLE BOARD LAYOUT

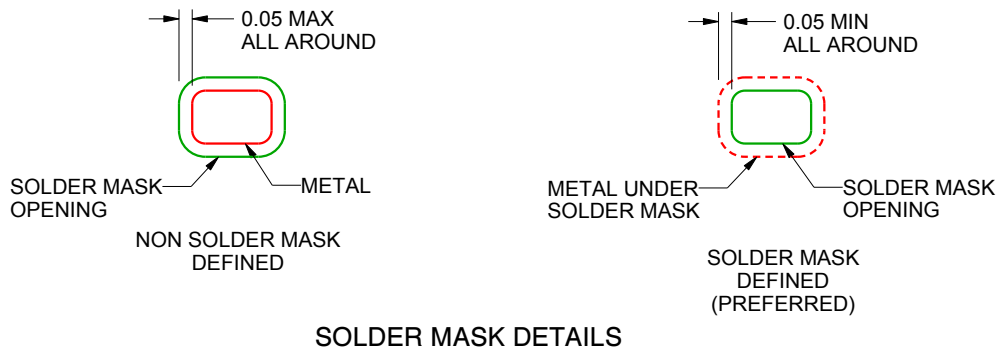
DRY0006B

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE  
1:1 RATIO WITH PKG SOLDER PADS  
SCALE:40X



SOLDER MASK DETAILS

4222207/B 02/2016

NOTES: (continued)

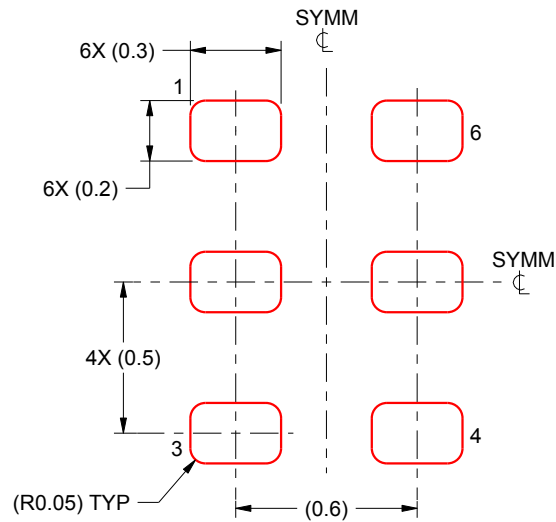
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).

# EXAMPLE STENCIL DESIGN

DRY0006B

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.075 - 0.1 mm THICK STENCIL  
SCALE:40X

4222207/B 02/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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最終更新日 : 2025 年 10 月